except that marked up versions are not being supplied for any added claim or canceled claim.

Sub F1 E1

65. (three times amended) An integrated circuit comprising:

a monocrystalline silicon substrate;

a roughened platinum layer over the substrate, the roughened platinum layer having a continuous surface characterized by columnar pedestals that are at least about 300Å tall and have an average diameter of at least about 200 Å; and

an intervening layer between the platinum layer and the substrate, the intervening layer comprising at least one of IrO_2, RuO_2, RhO_2, or OsO_2.

Sub F1 E2

74. (twice amended) A capacitor comprising:

a first capacitor electrode over a monocrystalline silicon substrate;

a second capacitor electrode;

a dielectric layer between the first and second capacitor electrodes;

wherein at least one of the first and second capacitor electrodes comprise roughened platinum, the roughened platinum having a continuous surface characterized by columnar pedestals having heights greater than or equal to about one-third of a total thickness of the roughened platinum and having an average diameter of at least about 200 Å.

78. (twice amended) An integrated circuit comprising:

a semiconductive substrate;

a conductive node location disposed within the semiconductive substrate;

a first layer disposed over the semiconductive substrate and in electrical contact with the conductive node, the first layer comprising at least one of iridium, rhodium, ruthenium, palladium, osmium, silver, alloy, IrO_2, RuO_2, RhO_2, or OsO_2; and

a platinum alloy layer disposed over the first layer, the platinum alloy layer characterized by a continuous, roughened outer surface, the platinum alloy layer comprising platinum and at least one of rhodium, iridium, ruthenium, palladium, osmium or silver, and the roughened platinum alloy layer comprising columnar pedestal structures having heights greater than or equal to about one-third of a total thickness of the roughened platinum alloy layer and having an average diameter of at least about 200 Å.